CORNERSTONE STANDARD COMPONENTS LIBRARY

(On 300 nm Si₃N₄ Platform)







Preface

In this document, we summarise the up-to-date designs and their measurement results of our CORNERSTONE standard components on SiN platforms, at the same time we are optimising the current designs, adding in new designs, and gathering more measurement results.





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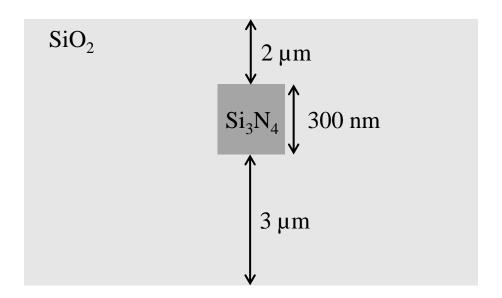
- Wavelength: 1550 nm
- Platform: 300 nm Si₃N₄





- Wavelength: 1550 nm
- Platform: 300 nm Si₃N₄

• STRIP

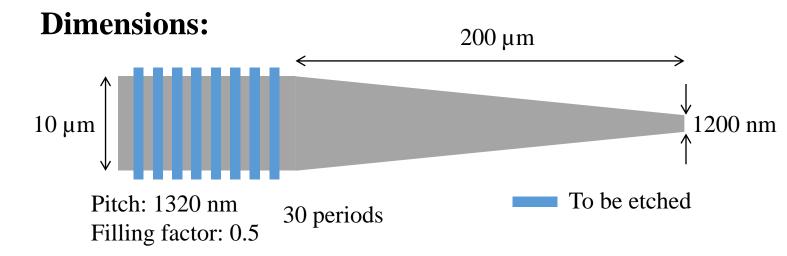






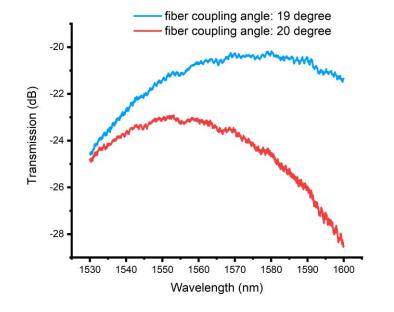
SiN300nm_1550nm_TE_STRIP_Grating_Coupler

Platform:	$300 \text{ nm Si}_3 N_4$
Wavelength:	1550 nm
Etching depth:	300 nm
Polarization:	TE
Cell name in GDS lib:	SiN300nm_1550nm_TE_STRIP_Grating_Coupler



Fiber coupling angle: 19-20 degree

Measured transmission spectrum



Transmission measured on a test structure as below, which includes two gratings.



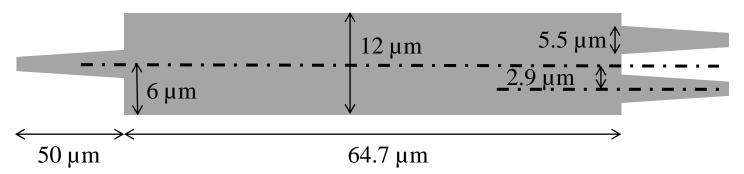




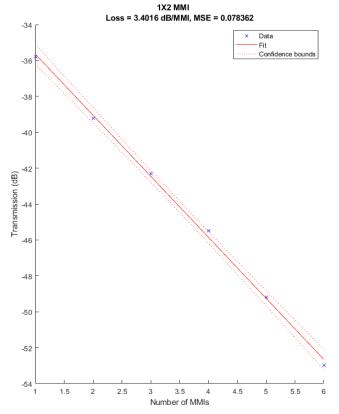
SiN300nm_1550nm_TE_STRIP_2x1_MMI

Platform:	$300 \text{ nm Si}_3 N_4$
Wavelength:	1550 nm
Etching depth:	300 nm
Polarization:	TE
Cell name in GDS lib:	SiN300nm_1550nm_TE_STRIP_2x1_MMI

Dimensions:



Measurement results:



Transmission includes the measurement system loss, grating coupler loss and waveguide loss, as well as the measured device loss

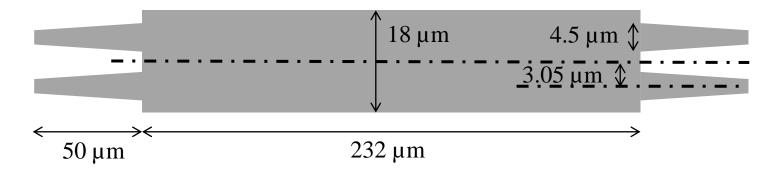




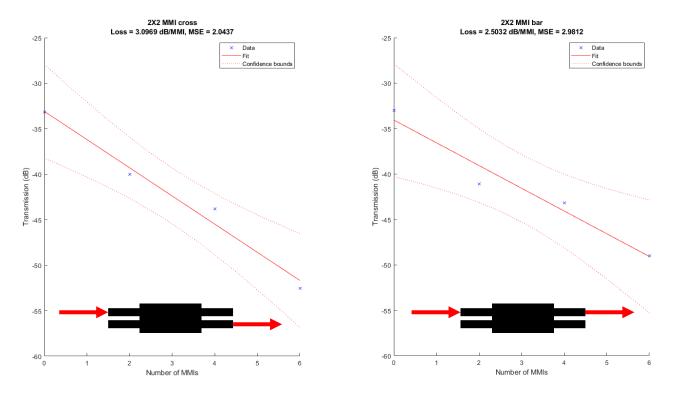
SiN300nm_1550nm_TE_STRIP_2x2_MMI

Platform:	$300 \text{ nm Si}_3 N_4$
Wavelength:	1550 nm
Etching depth:	300 nm
Polarization:	TE
Cell name in GDS lib:	SiN300nm_1550nm_TE_STRIP_2x2_MMI

Dimensions:



Measurement results:







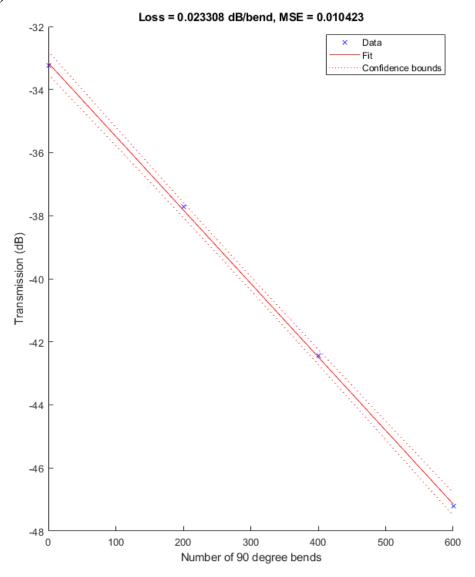
SiN300nm_1550nm_TE_STRIP_90_Degree_Bend

Platform:	300 nm Si ₃ N ₄
Wavelength:	1550 nm
Etching depth:	300 nm
Polarization:	TE
Cell name in GDS lib:	SiN300nm_1550nm_TE_STRIP_90_Degree_Bend

(Suggested bend radius: 80 um)

Measurement results:

(per 90° bend)







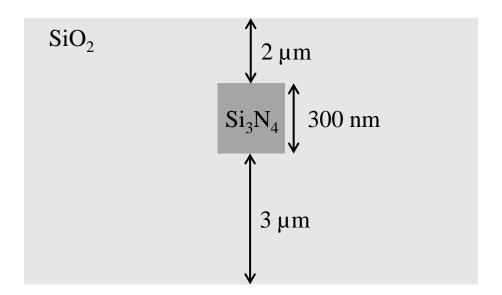
- Wavelength: 1310 nm
- Platform: 300 nm Si₃N₄





- Wavelength: 1310 nm
- Platform: 300 nm Si₃N₄

• STRIP

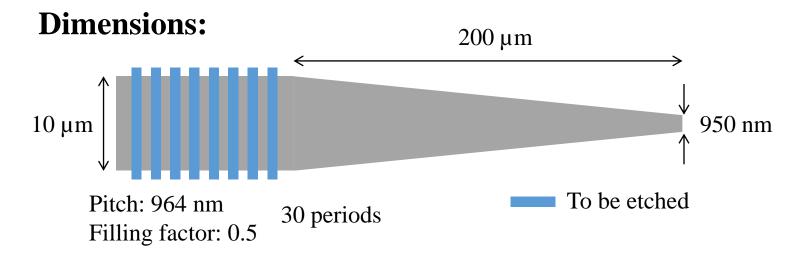






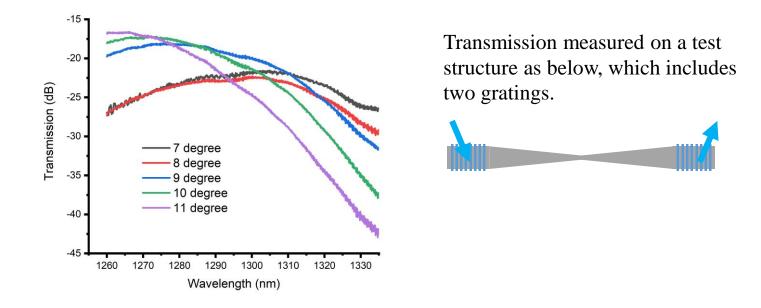
SiN300nm_1310nm_TE_STRIP_Grating_Coupler

Platform:	$300 \text{ nm Si}_3 N_4$
Wavelength:	1310 nm
Etching depth:	300 nm
Polarization:	TE
Cell name in GDS lib:	SiN300nm_1310nm_TE_STRIP_Grating_Coupler



Fiber coupling angle: 7-11 degree

Measured transmission spectrum



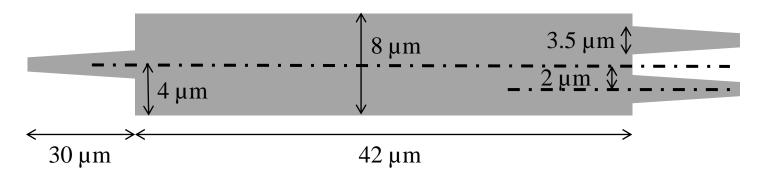




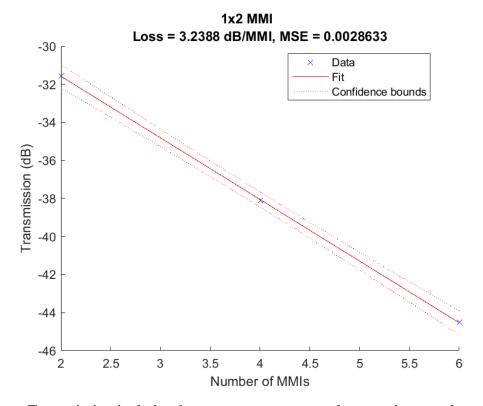
SiN300nm_1310nm_TE_STRIP_2x1_MMI

Platform:	$300 \text{ nm Si}_3 N_4$
Wavelength:	1310 nm
Etching depth:	300 nm
Polarization:	TE
Cell name in GDS lib:	SiN300nm_1310nm_TE_STRIP_2x1_MMI

Dimensions:



Measurement results:



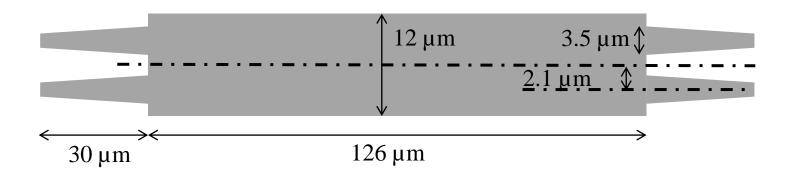




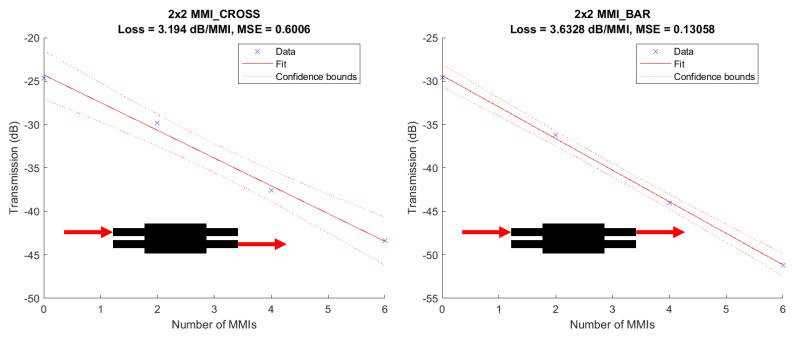
SiN300nm_1310nm_TE_STRIP_2x2_MMI

Platform:	$300 \text{ nm Si}_3 N_4$
Wavelength:	1310 nm
Etching depth:	300 nm
Polarization:	TE
Cell name in GDS lib:	SiN300nm_1310nm_TE_STRIP_2x2_MMI

Dimensions:



Measurement results:







SiN300nm_1310nm_TE_STRIP_90_Degree_Bend

Platform:	300 nm Si ₃ N ₄
Wavelength:	1310 nm
Etching depth:	300 nm
Polarization:	TE
Cell name in GDS lib:	SiN300nm_1310nm_TE_STRIP_90_Degree_Bend

(Suggested bend radius: 60 um)

Measurement results:

(per 90° bend)

